

(19) World Intellectual Property Organization
International Bureau(43) International Publication Date
21 December 2000 (21.12.2000)

PCT

(10) International Publication Number
WO 00/77548 A1(51) International Patent Classification⁷: G02B 6/132

(GB). HEATON, John, Michael [GB/GB]; DERA Malvern, St. Andrews Road, Malvern, Worcestershire WR14 3PS (GB).

(21) International Application Number: PCT/GB00/02145

(22) International Filing Date: 2 June 2000 (02.06.2000)

(74) Agent: BOWDERY A.O.; D/IPR, DERA Formalities, A4 Bldg., Ively Road, Farnborough, Hampshire GU14 0LX (GB).

(25) Filing Language: English

(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW.

(26) Publication Language: English

(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

(30) Priority Data:

9913713.5 14 June 1999 (14.06.1999) GB
9918097.8 3 August 1999 (03.08.1999) GB

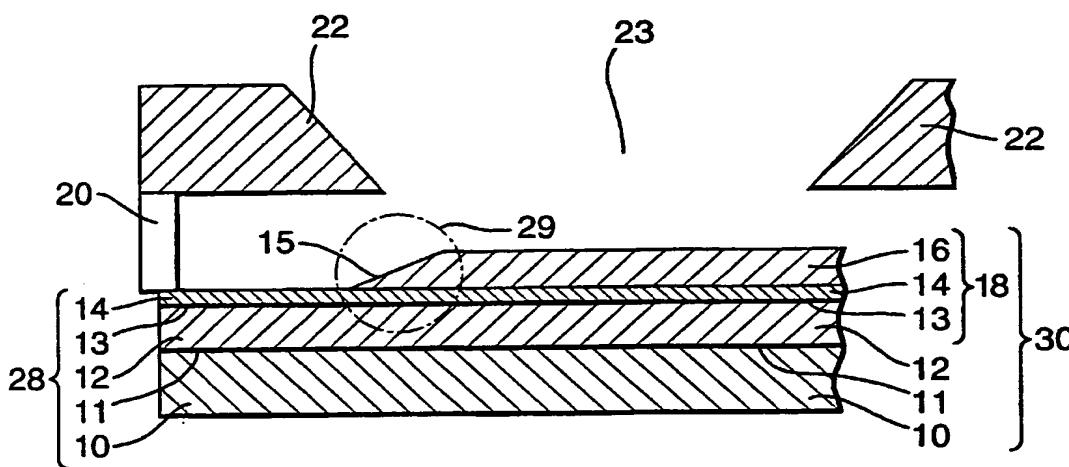
(71) Applicant (for all designated States except US): THE SECRETARY OF STATE FOR DEFENCE [GB/GB]; Defence Evaluation and Research Agency, A4 Building, Ively Road, Farnborough, Hampshire GU14 0LX (GB).

Published:

— With international search report.

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD OF FABRICATING A SEMICONDUCTOR DEVICE



WO 00/77548 A1

(57) Abstract: A method of fabricating a semiconductor device includes a step of growing at least one tapered epitaxial layer upon a supporting surface by chemical beam epitaxy, the plane of the taper being inclined to the supporting surface.